

Amendments to the Specification

Please replace the paragraph beginning on page 1, third full paragraph and ending on page 2, line 1, with the following rewritten paragraph:

In a process of manufacturing an integrated circuit or a thin-film transistor, etc., generally, a silicon thin-film has been formed by a CVD method, using a ~~monosilan~~ monosilane gas or a ~~disilan-disilane~~ gas. A polysilicon thin-film is formed by a thermal CVD method and an amorphous silicon thin-film is formed by a plasma-activated CVD method. Then, in order to obtain a predetermined pattern of a silicon thin-film, after forming a silicon thin-film on an entire substrate, a patterning process, which removes an unnecessary part by photolithography and etching using a resist, has been performed.

Please replace the paragraph, beginning on page 2, last paragraph and ending on page 3, line 7, with the following rewritten paragraph:

Meanwhile, the Japanese Patent Laid-Open Publication No. 2000-12465 discloses a method of arranging a first silicon film-formed body and a second silicon film-formed body, on a film-forming surface of which a liquid material is applied, both film-forming surfaces facing each other, thereby forming at the same time a silicon film on both film-forming surfaces of the first silicon film formed body and the second silicon film formed body. As a liquid material, liquid silane, which is a silicide not containing carbon and indicated by the general formula $\text{Si}_n\text{H}_{2n+2}$ or Si_nH_{2n} ($3 \leq n \leq 7$), is used.

Please replace the paragraph beginning on page 5, second full paragraph, with the following rewritten paragraph:

The first embodiment relates to a first invention which forms a silicon thin-film by ~~proving~~ providing a thin-film-forming surface and a liquid-arranging surface on a same surface of a substrate. The concept of the present invention is as follows:

Please cancel the paragraph at page 8, third full paragraph.

Please replace the paragraph beginning on page 15, first full paragraph, with the following rewritten paragraph:

In the second embodiment of the present invention, a liquid arranging surface is provided on a first substrate and a silicon thin-film is formed on the thin-film-forming surface of a second substrate. ~~The concept of the present invention becomes bellows.~~ The definitions of terms and transformation examples are the same as used in the first invention of the first embodiment; therefore, those used in the first embodiment are also adopted in a second invention.

Please replace the paragraph beginning on page 16, last paragraph, and ending on page 17, line 13, with the following rewritten paragraph:

First, two glass substrates are prepared, and on one side of each of the surfaces of both glass substrates, a pattern comprising a monomolecular film (self-assembled film) is formed by the same method as in the first invention, using FAS 13. That is, the method of the first embodiment was applied to a liquid arranging surface 81 of a first substrate 8 and a thin-film-forming surface 71 of a second substrate 7 to form patterns 30a and 30b of a monomolecular film which have a same form when they were facing each other (cf. ~~ST1-STEP 1~~ in figure 2). For example, a photomask, in which a round ultraviolet ray transmission part having the diameter of 50 μm was reticularly arranged at the pitch of 5 mm, was used. By using such photomask, the monomolecular film patterns 30a and ~~31b~~ 30B also have a form in which a round opening 31 is reticularly arranged. Here, alignment marks were formed in the four corners of the photomask and such marks were transcribed to the monomolecular film patterns 30a and 30b, which is a preferred manner.

Please replace the paragraph beginning on page 17, first full paragraph, with the following rewritten paragraph:

Next, by the same method as in the first embodiment, liquid is arranged on the first substrate. That is, the first substrate 8 was arranged in a nitrogen gas atmosphere such that the surface (liquid arranging surface) 81, on which a monomolecular film pattern 30a was formed, facing upwards. Then, the same liquid (cyclosilane solution) as in the first embodiment was discharged by an inkjet method into all openings 31 of the monomolecular pattern 30a to arrange a droplet 5 (cf. ST1-STEP 1 of figure 2).

Please replace the paragraph beginning on page 17, last paragraph and ending on page 18, line 8, with the following rewritten paragraph:

Next, the thin-film-forming surface of the second substrate is arranged to be set facing the liquid arranging surface of the first substrate. That is, as shown in ST1-STEP 1 of figure 2, the second substrate 7 was arranged such that the thin-film-forming surface 71, on which a monomolecular film pattern 30b was formed, faces downwards and was set above and in parallel with the first substrate 8 at a predetermined distance (e.g. 1 mm). In the case of this arrangement, alignment marks formed on the monomolecular film patterns 30a and 30b of the substrates 7 and 8 were aligned and the opening 31, in which the thin-film-forming surface 71 of the monomolecular film pattern 30b of the second substrate 7 was exposed, and the opening 31, in which the droplet 5 in the monomolecular film pattern 30a of the first substrate 8 was arranged, were aligned.

Please replace paragraph beginning on page 18, second full paragraph, with the following rewritten paragraph:

For example, as shown in ST2-STEP 2 of figure 2, while running a nitrogen gas between substrates 7 and 8 and in parallel with the substrate surface, the second substrate 7 was heated to a temperature at which a vaporizing matter of silicide can be decomposed, for example 450 °c, and retained for 10 minutes. Thus, the first substrate 8 was indirectly heated by the heat emitted from the second substrate 7 and a part of a droplet 5 on the first substrate

8 comprising the cyclosilane solution was vaporized and supplied into the opening 31 of the monomolecular pattern 30b of the second substrate 7.

Please replace the paragraph beginning on page 19, first full paragraph, with the following rewritten paragraph:

Gaseous cyclopentasilane and silylcyclopentasilane vaporized from the droplet 5 were decomposed by heat and silicon was deposited in the opening 31 of the monomolecular pattern 30b of the second substrate 7 and, as shown in ~~ST3~~STEP 3 of figure 2, a silicon thin-film 50 was formed in this opening 31. The silicon thin-film 50 is not formed on the surface (the part in which a monomolecular film remains) of the monomolecular film pattern 30b. The thickness of the silicon thin-film 50 was 50 nm.